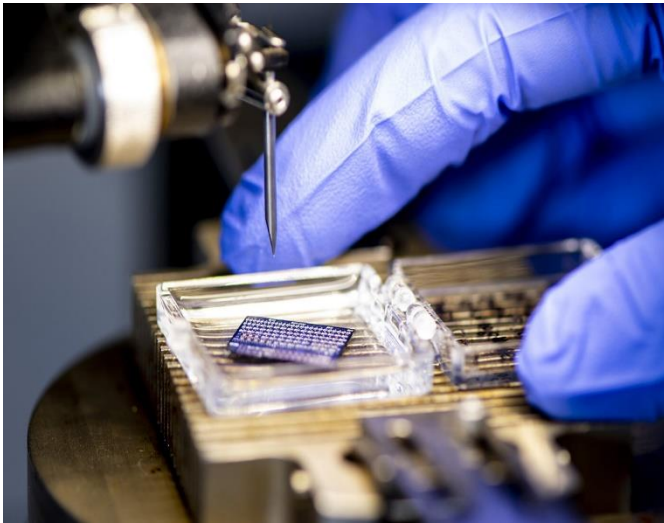


# IP MARKETPLACE

## CONNECTING INNOVATION TO YOUR BUSINESS

### TECH OFFER

## A COMPLEMENTARY METAL-OXIDE SEMICONDUCTOR



### ▶ MORE INFORMATION

#### MEGA-TREND

- Innovative Technologies of the Future
- Chemicals and Materials
- Energy and Power
- Automotive
- Electronics and Security

#### TECHNOLOGY READINESS LEVEL (TRL)

- TRL 5 (Lab Prototype - Field Testing)

#### PATENT/ GRANTED NUMBER

- PI 2021003911

### ▶ TECHNOLOGY OVERVIEW

The present invention relates to a complementary metal-oxide semiconductor for performing logical functions. The complementary metal-oxide semiconductor comprises a wafer, an oxide layer, an interfacial layer and a plurality of metal terminals. The wafer is configured as a base for the complementary metal-oxide semiconductor. The oxide layer is deposited onto interfacial layer as an electrical insulator for the wafer. The interfacial layer is configured to bind the wafer with the oxide layer. The plurality of metal terminals is configured as a point of contact for source terminals, drain terminals, and gate input.

## CONTACT US!

Dr. Lee Ching Shya

UMCIE Business Officer

Email: [leecs@um.edu.my](mailto:leecs@um.edu.my)

Phone: +603 – 7967 7351 / 7352